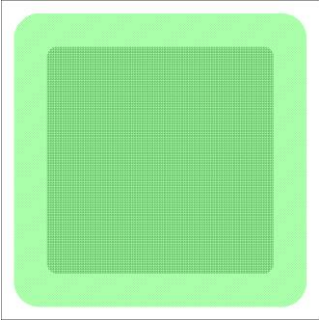


SiC Silicon-Carbide**1700V 5A Schottky Diode**

Bonding Pad Information		Chip Information	
		Die Size (With Scribe Line)	2,360μm x 2,360μm
		Anode Pad Size	1,810μm x 1,810μm
		Scribe Line Size	100μm
		Wafer Size	4inchs
		Wafer Thickness	350μm
		Gross Die	1,147ea
		Metallization	Front Side Al/Cu : 4.0μm
		Back Side	Ti/Ni/Ag : 2.0μm

Maximum Ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	1700	V
Surge Peak Reverse Voltage	V _{RSM}	1700	V
DC Current @ T _J =150°C	I _F	5	A
Operating Junction and Storage Temperature Range	T _J	-55 to 175	°C

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
DC Blocking Voltage	V _R	I _R =100uA	1700	2000	-	V
Forward Voltage	V _F	I _F =5A, T _J =25°C	-	1.4	1.7	V
		I _F =5A, T _J =175°C	-	1.9	2.4	
Reverse Current	I _R	V _R =1700V, T _J =25°C	-	6	20	μA
Total Capacitive Charge	Q _C	V _R =1700V, T _J =25°C $Q_C = \int_0^{V_R} C(V) dV$	-	60	-	nC
Total Capacitance	C _j	V _R =0.1V, f=1MHz	-	386	-	pF
		V _R =800V, f=1MHz	-	29	-	
		V _R =1700V, f=1MHz	-	28	-	